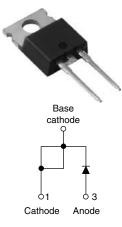


### Vishay High Power Products

## **HEXFRED® Ultrafast Soft Recovery Diode, 25 A**



|  | -22 |  |  |
|--|-----|--|--|
|  |     |  |  |

| PRODUCT SUMMARY                    |          |  |  |  |  |
|------------------------------------|----------|--|--|--|--|
| V <sub>R</sub>                     | 600 V    |  |  |  |  |
| V <sub>F</sub> at 25 A at 25 °C    | 1.7 V    |  |  |  |  |
| I <sub>F(AV)</sub>                 | 25 A     |  |  |  |  |
| t <sub>rr</sub> (typical)          | 23 ns    |  |  |  |  |
| T <sub>J</sub> (maximum)           | 150 °C   |  |  |  |  |
| Q <sub>rr</sub> (typical)          | 112 nC   |  |  |  |  |
| dl <sub>(rec)M</sub> /dt (typical) | 250 A/µs |  |  |  |  |
| I <sub>RRM</sub>                   | 10 A     |  |  |  |  |

#### **FEATURES**

- · Ultrafast recovery
- · Ultrasoft recovery
- Very low I<sub>RRM</sub>
- Very low Q<sub>rr</sub>
- · Specified at operating conditions
- · Designed and qualified for industrial level

#### **BENEFITS**

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

HFA25TB60 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the HFA25TB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA25TB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

| ABSOLUTE MAXIMUM RATINGS                         |                                   |                         |               |       |  |  |
|--|-----------------------------------|-------------------------|---------------|-------|--|--|
| PARAMETER  | SYMBOL                            | TEST CONDITIONS         | VALUES        | UNITS |  |  |
| Cathode to anode voltage                         | V <sub>R</sub>                    |                         | 600           | V     |  |  |
| Maximum continuous forward current               | I <sub>F</sub>                    | T <sub>C</sub> = 100 °C | 25            |       |  |  |
| Single pulse forward current                     | I <sub>FSM</sub>                  |                         | 225           | Α     |  |  |
| Maximum repetitive forward current               | I <sub>FRM</sub>                  |                         | 100           |       |  |  |
| Maximum names dissination                        | В                                 | T <sub>C</sub> = 25 °C  | 125           | w     |  |  |
| Maximum power dissipation                        | $P_D$                             | T <sub>C</sub> = 100 °C | 50            | ]     |  |  |
| Operating junction and storage temperature range | T <sub>J</sub> , T <sub>Stg</sub> |                         | - 55 to + 150 | °C    |  |  |

# **HFA25TB60**

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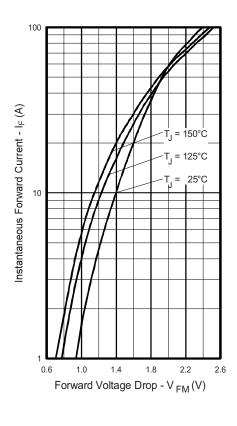
| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                 |  |            |      |      |      |       |
|--|-----------------|--|------------|------|------|------|-------|
| PARAMETER  | SYMBOL          | TEST CONDITIONS  |            | MIN. | TYP. | MAX. | UNITS |
| Cathode to anode breakdown voltage   | V <sub>BR</sub> | Ι <sub>R</sub> = 100 μΑ  |            | 600  | -    | -    |       |
|  | V <sub>FM</sub> | I <sub>F</sub> = 25 A  | See fig. 1 | -    | 1.3  | 1.7  | V     |
| Maximum forward voltage  |                 | I <sub>F</sub> = 50 A  |            | -    | 1.5  | 2.0  |       |
|  |                 | I <sub>F</sub> = 25 A, T <sub>J</sub> = 125 °C                         |            | -    | 1.3  | 1.7  |       |
| Maximum reverse  |                 | $V_R = V_R$ rated  | See fig. 2 | -    | 1.5  | 20   | μA    |
| leakage current  | I <sub>RM</sub> | $T_J = 125  ^{\circ}\text{C},  V_R = 0.8  \text{x}  V_R  \text{rated}$ | See lig. 2 | -    | 600  | 2000 | μΑ    |
| Junction capacitance   | C <sub>T</sub>  | V <sub>R</sub> = 200 V   | See fig. 3 | =    | 55   | 100  | pF    |
| Series inductance L <sub>S</sub> Measured lead to lead 5 mm from package boo         |                 | ackage body  | -          | 8.0  | -    | nH   |       |

| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                           |  |  |      |      |      |        |
|---|---------------------------|--|--|------|------|------|--------|
| PARAMETER   | SYMBOL                    | TEST CONDITIONS  |  | MIN. | TYP. | MAX. | UNITS  |
|   | t <sub>rr</sub>           | $I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ |  | -    | 23   | -    |        |
| Reverse recovery time See fig. 5, 6 and 16  | t <sub>rr1</sub>          | T <sub>J</sub> = 25 °C   | $I_F = 25 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$ | -    | 50   | 75   | ns     |
|   | t <sub>rr2</sub>          | T <sub>J</sub> = 125 °C  |  | -    | 105  | 160  |        |
| Peak recovery current<br>See fig. 7 and 8   | I <sub>RRM1</sub>         | T <sub>J</sub> = 25 °C   |  | -    | 4.5  | 10   | A nC   |
|   | I <sub>RRM2</sub>         | T <sub>J</sub> = 125 °C  |  | -    | 8.0  | 15   |        |
| Reverse recovery charge<br>See fig. 9 and 10  | Q <sub>rr1</sub>          | T <sub>J</sub> = 25 °C   |  | -    | 112  | 375  |        |
|   | Q <sub>rr2</sub>          | T <sub>J</sub> = 125 °C  |  | -    | 420  | 1200 | IIC    |
| Peak rate of fall of recovery current during t <sub>b</sub> See fig. 11 and 12              | dI <sub>(rec)M</sub> /dt1 | T <sub>J</sub> = 25 °C   |  | -    | 250  | -    | - A/μs |
|   | dI <sub>(rec)M</sub> /dt2 | T <sub>J</sub> = 125 °C  |  | -    | 160  | -    |        |

| THERMAL - MECHANICAL SPECIFICATIONS     |                   |  |              |      |            |                        |
|---|-------------------|--|--------------|------|------------|------------------------|
| PARAMETER                               | SYMBOL            | TEST CONDITIONS                            | MIN.         | TYP. | MAX.       | UNITS                  |
| Lead temperature                        | T <sub>lead</sub> | 0.063" from case (1.6 mm) for 10 s         | -            | -    | 300        | °C                     |
| Thermal resistance, junction to case    | R <sub>thJC</sub> |  | -            | -    | 1.0        |                        |
| Thermal resistance, junction to ambient | R <sub>thJA</sub> | Typical socket mount                       | -            | -    | 80         | K/W                    |
| Thermal resistance, case to heatsink    | R <sub>thCS</sub> | Mounting surface, flat, smooth and greased | -            | 0.5  | -          |                        |
| Weight                                  |                   |  | -            | 2.0  | -          | g                      |
| vveigni                                 |                   |  | -            | 0.07 | -          | OZ.                    |
| Mounting torque                         |                   |  | 6.0<br>(5.0) | -    | 12<br>(10) | kgf · cm<br>(lbf · in) |
| Marking device                          |                   | Case style TO-220AC                        | HFA25TB60    |      |            |                        |



# HEXFRED® Vishay High Power Products Ultrafast Soft Recovery Diode, 25 A



10000

(V) 1000

TJ = 125°C

TJ = 25°C

0.01

0 100 200 300 400 500 600

Reverse Voltage - V<sub>R</sub> (V)

Fig. 2 - Typical Reverse Current vs. Reverse Voltage

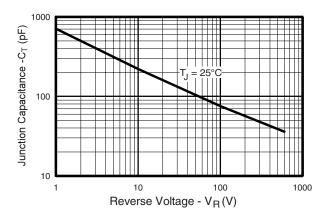


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

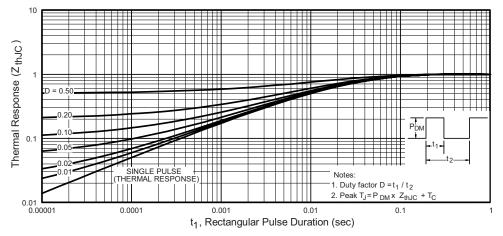


Fig. 4 - Maximum Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

## Vishay High Power Products

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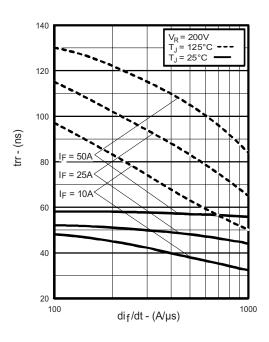


Fig. 5 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

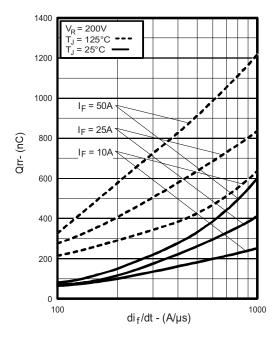


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

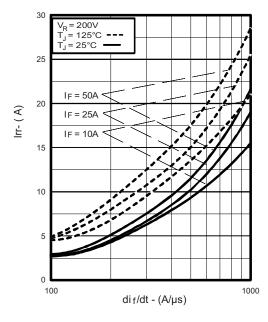


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

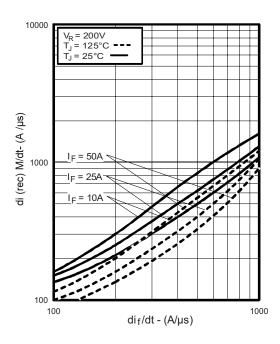


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt



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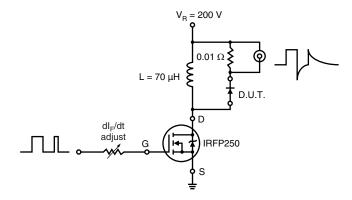
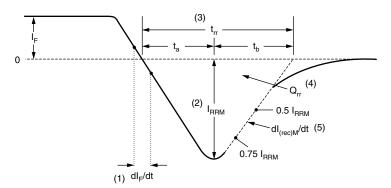


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{r}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

| LINKS TO RELATED DOCUMENTS                 |                                 |  |  |  |
|--|---------------------------------|--|--|--|
| Dimensions http://www.vishay.com/doc?95221 |                                 |  |  |  |
| Part marking information                   | http://www.vishay.com/doc?95224 |  |  |  |



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